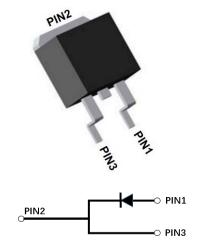


YJD117010BG1

RoHS COMPLIANT

Silicon Carbide Schottky Diode

V _{RRM}	1700V
I _{F (135°C)}	16A
Q _c	110nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D117010BG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1700
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	1700
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	1700
Continuous forward current @ $T_c=25^{\circ}C$			32
Continuous forward current @ T _c =135°C	I _F	А	16
Continuous forward current @ T _c =157°C			10
Non-repetitive peak forward surge current $@ T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	130
Power Dissipation@ T _c =25°C	P	w	197
Power Dissipation@ T _c =110°C	P _{TOT}	vv	86
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	85
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



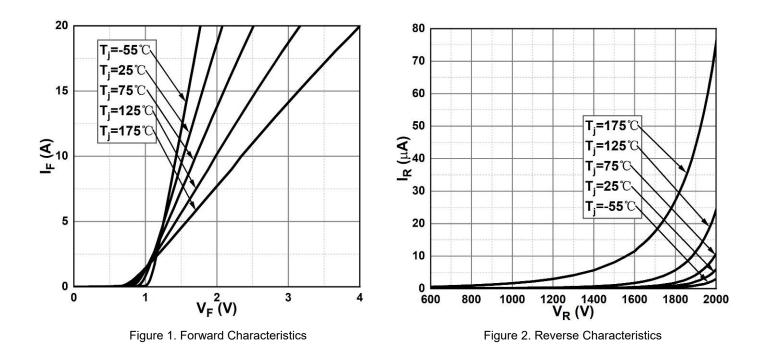
Electrical Characteristics

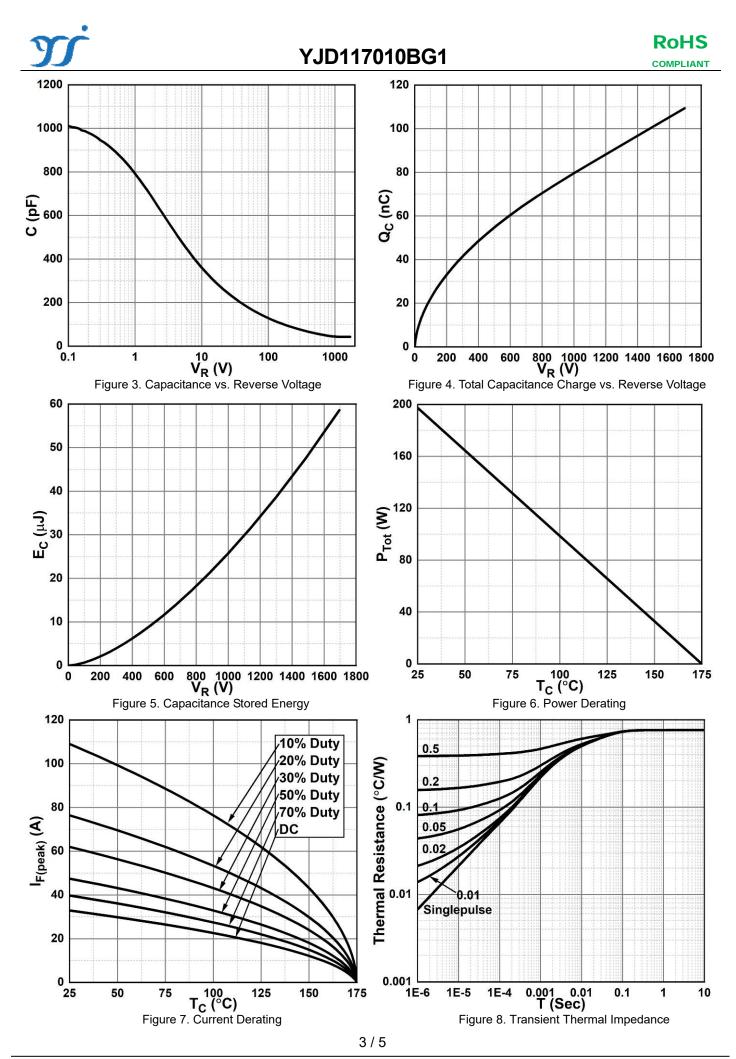
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Forward valtage dran	N N		I _F =10A, T _j =25°C	1.51	1.65		
Forward voltage drop	VF	V	I _F =10A, T _j =175°C	2.3	-		
Povereo lockero surrent			V _R =1700V, T _j =25°C	2	20		
Reverse leakage current	I _R	μΑ	V _R =1700V, T _j =175°C	20	-		
Total capacitive charge	Qc	nC	V_R =1700V, T _j =25°C , Q_C = $\int_0 V_R C(V) dV$	110	-		
		pF	V _R =0V, f=1MHZ	1038	-		
Total capacitance	С р		pF	pF	V _R =800V, f=1MHZ	47	-
			V _R =1700V, f=1MHZ	43	-		
Capacitance Stored Energy	Ec	μJ	V _R =1700V	57	-		

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	0.76

■Typical Characteristics

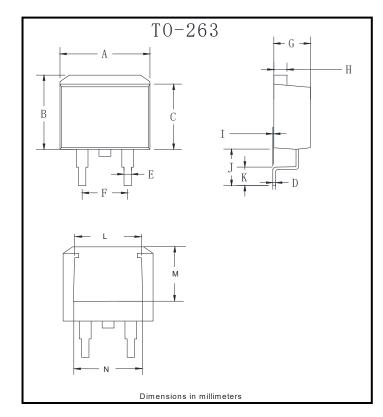




Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
E	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		

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Disclaimer

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